

SPECIFICATION

Device Name : IGBT Module

Type Name : 7MBR50SB120-01

Spec. No. : MS6M 0555

Date : Jun. - 02 - 2000

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Matsumoto Factory

	DATE	NAME	APPROVED	Fuji Electric Co., Ltd.		
DRAWN	Jun. - 2 - '00	<i>J. Kobayashi</i>		DWG. NO.	MS6M 0555	1 / 10
CHECKED	June - 2 - 00	<i>S. MATSUDA</i>	<i>J. Higashimura</i>			a

Revised Records

Date	Classi- fication	Ind.	Content	Applied date	Drawn	Checked	Approved
Jun.-2-'00	enactment	—	—	Issued date	—	S. Motta	J. Miyasaka
Jun.-14-'00	Revision	a	Revised type miss (P5/10)		J. Kobayashi	S. Motta	J. Miyasaka

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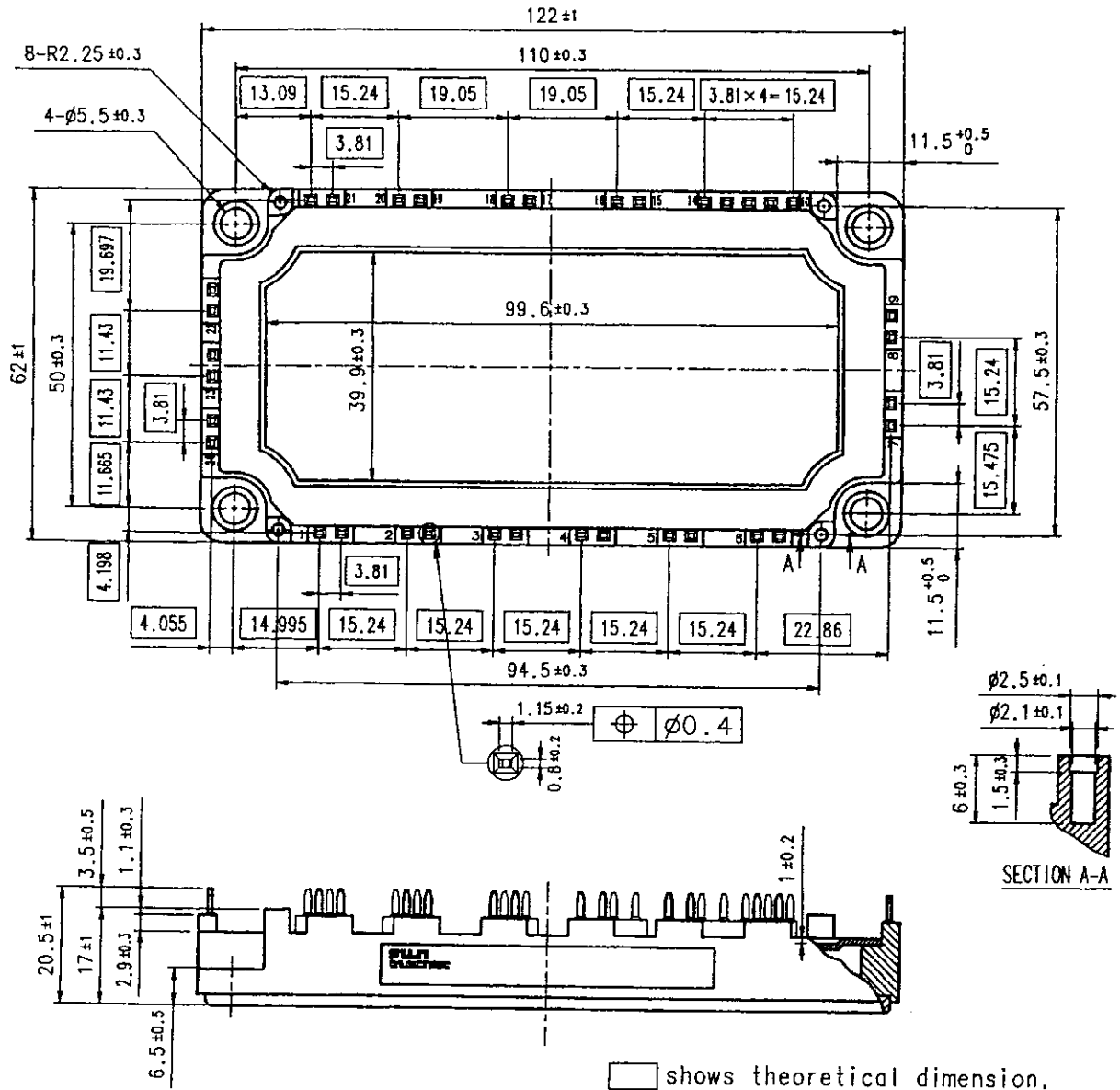
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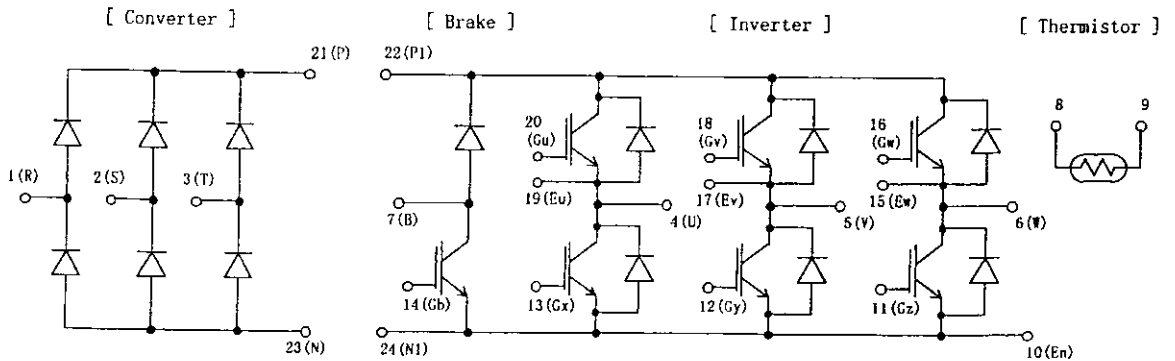
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1. Outline Drawing (Unit : mm)



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2. Equivalent circuit



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3. Absolute Maximum Ratings (at Tc= 25C unless otherwise specified)

Items		Symbols	Conditions	Maximum Ratings	Units	
Inverter	Collector-Emitter voltage	V _{CES}		1200	V	
	Gate-Emitter voltage	V _{GES}		+20	V	
	Collector current	I _c	Continuous	T _c =25C	75	A
				T _c =80C	50	
		I _{cp}	1ms	T _c =25C	150	A
				T _c =80C	100	
-I _c			50	A		
Collector Power Dissipation	P _c	1 device	360	W		
Brake	Collector-Emitter voltage	V _{CES}		1200	V	
	Gate-Emitter voltage	V _{GES}		+20	V	
	Collector current	I _c	Continuous	T _c =25C	35	A
				T _c =80C	25	
		I _{cp}	1ms	T _c =25C	70	A
				T _c =80C	50	
Collector Power Dissipation	P _c	1 device	180	W		
Repetitive peak reverse Voltage(Diode)	V _{RRM}		1200	V		
Converter	Repetitive peak reverse Voltage	V _{RRM}		1600	V	
	Average Output Current	I _o	50Hz/60Hz sine wave	50	A	
	Surge Current (Non-Repetitive)	I _{FSM}	T _j =150C,10ms	520	A	
	I ² t (Non-Repetitive)	I ² t	half sine wave	1352	A ² s	
	Junction temperature	T _j		150	C	
Storage temperature	T _{stg}		-40~ +125	C		
Isolation voltage	between terminal and copper base ^(*)	Viso	AC : 1min.	2500	V	
	between thermistor and others ^(*)			2500		
Mounting Screw Torque ^(*)				3.5	Nm	

(*) All terminals should be connected together when isolation test will be done.

(*) Terminal 8 and 9 should be connected together. Terminal 1 to 7 and 10 to 24 should be connected together and shorted to copper base.

(*) Recommendable Value : 2.5~3.5 Nm (M5)

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4. Electrical characteristics (at Tj= 25C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units			
			min.	typ.	Max.				
Inverter	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^(*) = 1200 V		1.0	mA			
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE = +20 V		200	nA			
	Gate-Emitter threshold voltage	VGE(th)	VCE = 20 V, Ic = 50 mA		5.5	7.2	8.5	V	
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, Ic = 50 A	chip terminal		2.1	2.3	2.7	V
	Input capacitance	Cies	VGE = 0 V, VCE = 10 V, f = 1 MHz		6000			pF	
	Turn-on time	ton	Vcc = 600 V		0.35	1.2		us	
		tr	Ic = 50 A		0.25	0.6			
		tr(0)	VGE = +15 V		0.1				
	Turn-off time	toff	RG = 24 ohm		0.45	1.0			
tf				0.08	0.3				
Forward on voltage	VF	IF = 50 A	chip terminal		2.3	2.5	3.3	V	
Reverse recovery time	trr	IF = 50 A				350	ns		
Brake	Zero gate voltage Collector current	ICES	VGE = 0 V, VCE ^(*) = 1200 V		1.0		mA		
	Gate-Emitter leakage current	IGES	VCE = 0 V, VGE = +20 V		200		nA		
	Collector-Emitter saturation voltage	VCE(sat)	VGE = 15 V, Ic = 25 A	chip terminal		2.1	2.25	2.7	V
	Turn-on time	ton	Vcc = 600 V		0.35	1.2		us	
		tr	Ic = 25 A		0.25	0.6			
	Turn-off time	toff	VGE = +15 V		0.45	1.0			
tf		RG = 51 ohm		0.08	0.3				
Reverse current	IRRM	VR = 1200 V				1.0	mA		
Converter	Forward on voltage	VFM	IF = 50 A	chip terminal		1.1	1.2	1.5	V
Reverse current	IRRM	VR = 1600 V				1.0	mA		
Thermistor	Resistance	R	T = 25C		5000			ohm	
			T = 100C		465	495	520		
	B value	B	T = 25/50C		3305	3375	3450	K	

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5. Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	Max.	
Thermal resistance (1 device)	Rth(j-c)	Inverter IGBT			0.35	C/W
		Inverter FWD			0.75	
		Brake IGBT			0.69	
		Converter Diode			0.50	
Contact Thermal resistance	Rth(c-f)	with Thermal Compound (*)		0.05		C/W

* This is the value which is defined mounting on the additional cooling fin with thermal compound.

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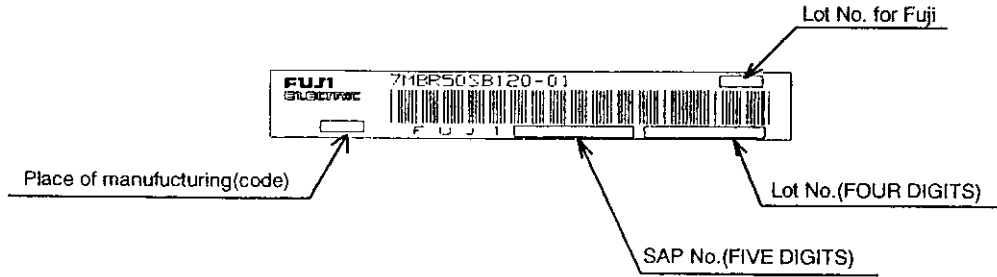
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6. Indication on module



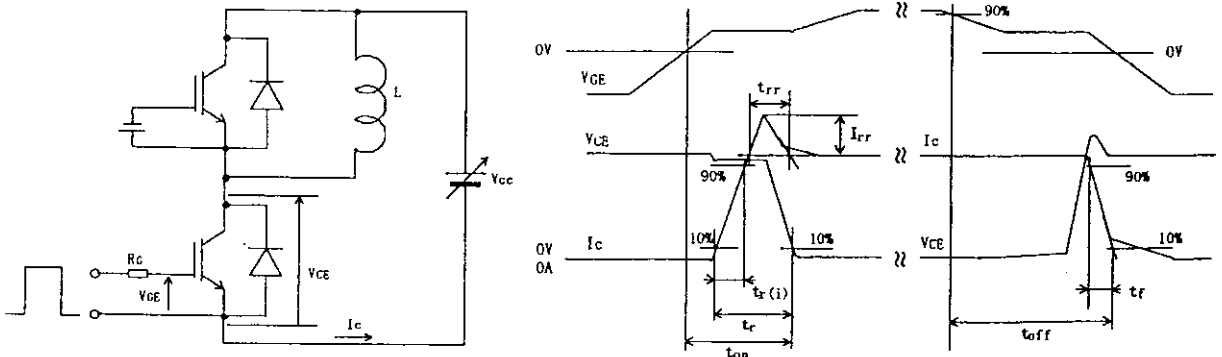
7. Applicable category

This specification is applied to Power Integrated Module named 7MBR50SB120-01 .

8. Storage and transportation notes

- The module should be stored at a standard temperature of 5 to 35°C and humidity of 45 to 75% .
- Store modules in a place with few temperature changes in order to avoid condensation on the module surface.
- Avoid exposure to corrosive gases and dust.
- Avoid excessive external force on the module.
- Store modules with unprocessed terminals.
- Do not drop or otherwise shock the modules when transporting.
- Please connect adequate fuse or protector of circuit between three-phase line and this product to prevent the equipment from causing secondary destruction.

9. Definitions of switching time



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